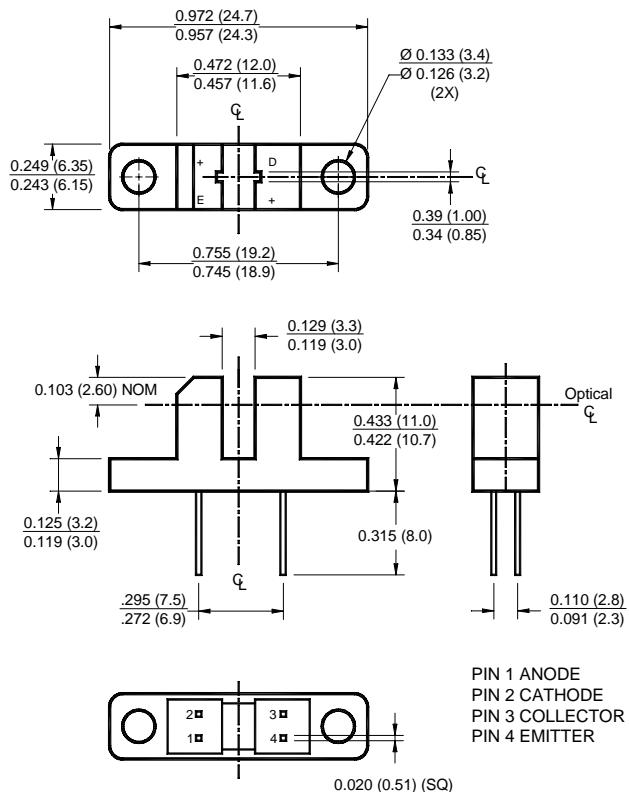
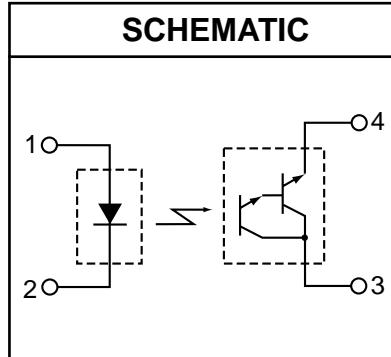
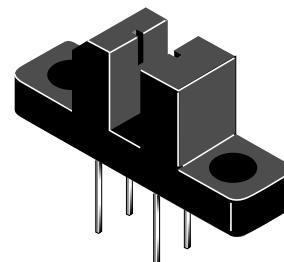


PACKAGE DIMENSIONS



NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



DESCRIPTION

The CNY29 is a gallium arsenide infrared emitting diode coupled with a silicon photo darlington in a plastic housing. The gap in the housing provides a means of interrupting the signal with tape, cards, shaft encoders, or other opaque material, switching the output from an "ON" to an "OFF" state.

FEATURES

- Opaque housing
- Low cost
- .035" apertures
- European "Pro Electron" registered

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	T_{OPR}	-55 to +100	°C
Storage Temperature	T_{STG}	-55 to +100	°C
Soldering Temperature (Iron) ^(2,3 and 4)	T_{SOL-I}	240 for 5 sec	°C
Soldering Temperature (Flow) ^(2 and 3)	T_{SOL-F}	260 for 10 sec	°C
INPUT (EMITTER)			
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	6	V
Power Dissipation ⁽¹⁾	P_D	100	mW
OUTPUT (SENSOR)			
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Collector Voltage	V_{ECO}	6	V
Collector Current	I_C	40	mA
Power Dissipation ($T_C = 25^\circ\text{C}$) ⁽¹⁾	P_D	150	mW

NOTE:

- Derate power dissipation linearly 1.67 mW/°C above 25°C.
- RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- Soldering iron tip 1/16" (1.6mm) minimum from housing.

ELECTRICAL / OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
INPUT (EMITTER)						
Forward Voltage	$I_F = 10 \text{ mA}$	V_F	—	—	1.7	V
Reverse Leakage Current	$V_R = 2 \text{ V}$	I_R	—	—	10	μA
OUTPUT (SENSOR)						
Emitter to Collector Breakdown	$I_E = 100 \text{ μA}, E_e = 0$	BV_{ECO}	7.0	—	—	V
Collector to Emitter Breakdown	$I_C = 10 \text{ mA}, E_e = 0$	BV_{CEO}	25	—	—	V
Collector to Emitter Leakage	$V_{CE} = 10 \text{ V}, E_e = 0$	I_{CEO}	—	—	100	nA
COUPLED						
On-State Collector Current	$I_F = 20 \text{ mA}, V_{CE} = 10 \text{ V}$	$I_{C(ON)}$	2.5	—	—	mA
Saturation Voltage	$I_F = 20 \text{ mA}, I_C = 0.5 \text{ mA}$	$V_{CE(SAT)}$	—	—	1.2	V
Turn-On Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$	t_{on}	—	150	—	μs
Turn-Off Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$	t_{off}	—	150	—	μs

TYPICAL PERFORMANCE CURVES

Figure 1. Output Current vs. Input Current

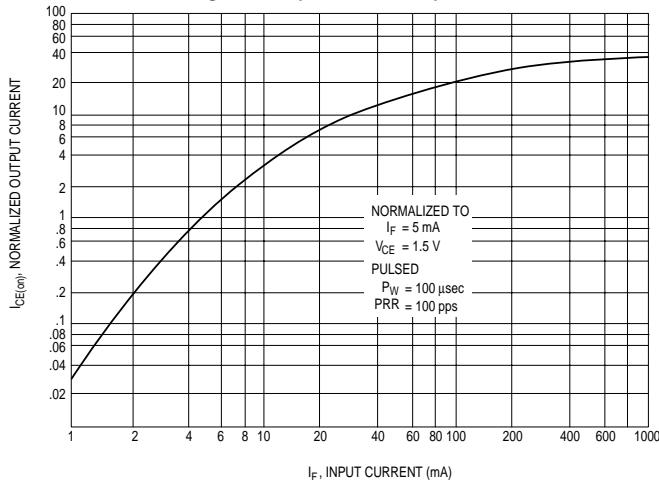


Figure 2. Output Current vs. Temperature

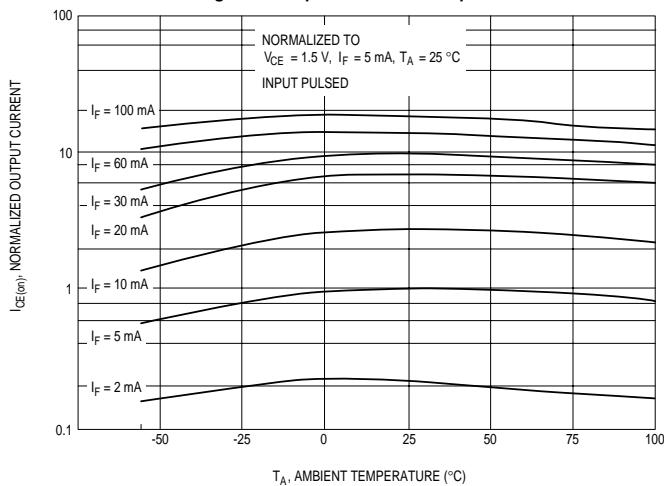
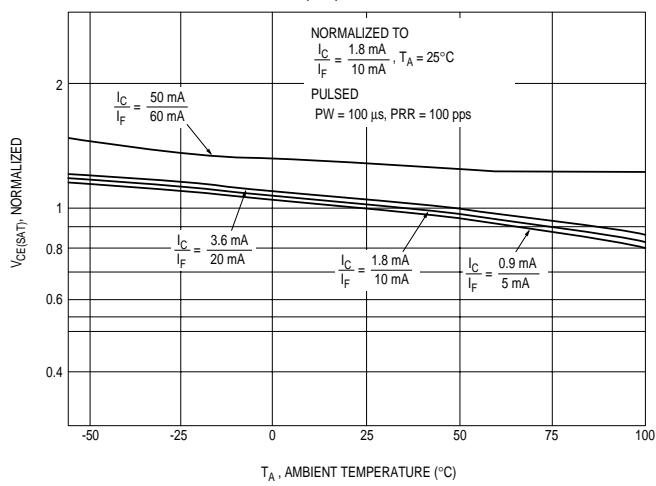


Figure 3. V_CE(SAT) vs. Temperature



TYPICAL PERFORMANCE CURVES (CONTINUED)

Figure 4. Leakage Current vs. Temperature

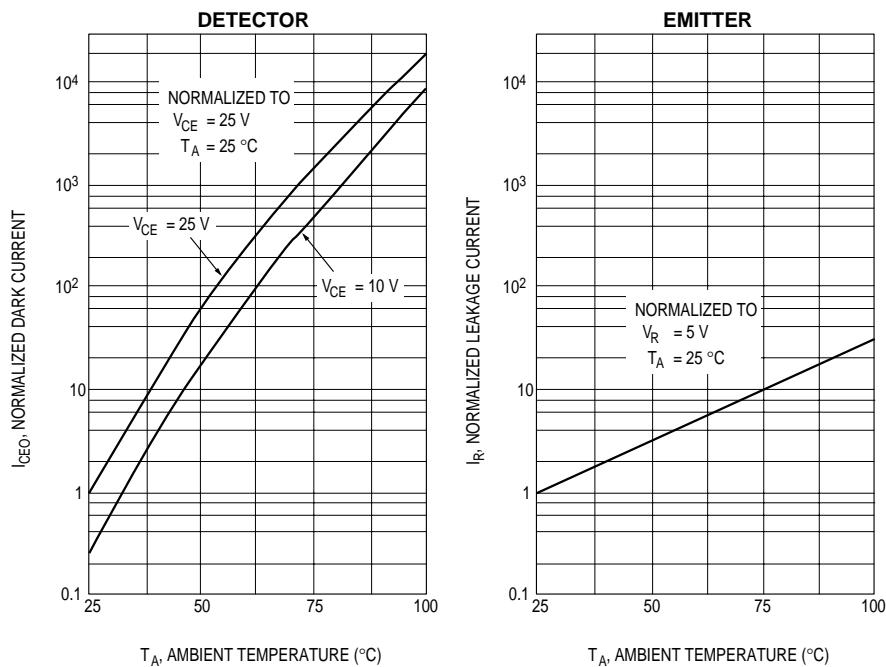


Figure 5. Switching Speed vs. R_L

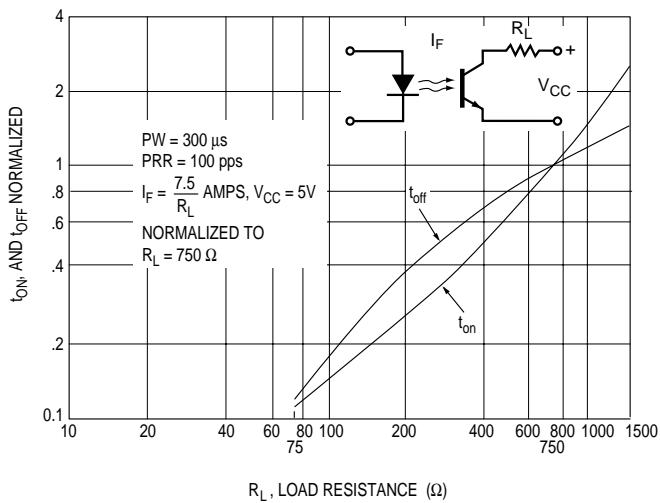
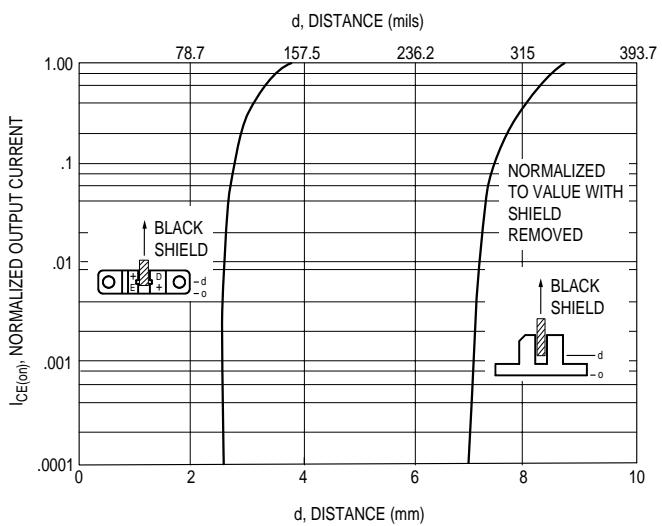


Figure 6. Output Current vs. Distance



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